

Application No.: 10/017,806

Docket No.: JCLA7567

In The Claims:

Please amend the claims as follows.

1. (currently amended) A method of monitoring dynamic particle pollution in an etching chamber, comprising the steps of:

providing a bare wafer coated with a photoresist;

positioning the bare wafer in an etching machine and performing an etching process on the photoresist, ~~wherein the etching process is carried out for 9 seconds to 15 seconds;~~ and

counting the amount of the particles on the bare etched wafer so as to determine polluted situation for the etching machine; and

cleaning the etching machine when a particle count of the etched bare wafer exceeds a control particle count.

Claim 2 (canceled).

3. (original) The method of claim 1, wherein the etching machine is a silicon nitride etching machine.

4. (original) The method of claim 1, wherein the etching machine is a silicon oxide etching machine.

5. (original) The method of claim 1, wherein the etching machine is a silicon oxynitride etching machine.

6. (original) The method of claim 1, wherein the etching machine is a polysilicon etching machine.

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7. (original) The method of claim 1, wherein the etching machine is a metal etching machine.

8. (original) The method of claim 1, wherein the step of performing etching process comprises:

transporting the bare wafer to a main etching chamber; and

turning on a plasma power source to perform the etching process on the photoresist.

9. (previously presented) The method of claim 8, wherein before the step of transporting the bare wafer to the main etch chamber further includes:

transporting the bare wafer from a port to a vacuum chamber; and

transporting the bare wafer from the vacuum chamber to a pre-alignment chamber.

10. (new) The method of claim 1, wherein the etching process is carried out for 9 seconds to 15 seconds.